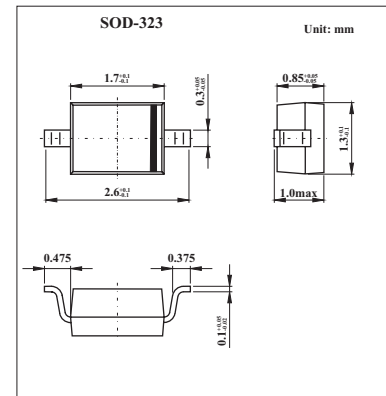


Silicon Epitaxial Planar Diode

1SV304

■ Features

- High Capacitance Ratio: $C_{1V}/C_{4V}=3.0$ (Typ.)
- Low Series Resistance: $r_s=0.27\ \Omega$ (Typ.)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	10	V
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R = 1\ \mu\text{A}$	10			V
Reverse Current	I_R	$V_R = 10\ \text{V}$			3	nA
Capacitance	C_{1V}	$f = 1\ \text{MHz}; V_R = 1\ \text{V}$	17.3	18.3	19.3	pF
	C_{4V}	$f = 1\ \text{MHz}; V_R = 4\ \text{V}$	5.3	6.1	6.6	
Capacitance Ratio	C_{1V}/C_{4V}		2.8	3		
Series Resistance	r_s	$V_R = 1\ \text{V}, f = 470\ \text{MHz}$		0.27	0.32	Ω

■ Marking

Marking	TV
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